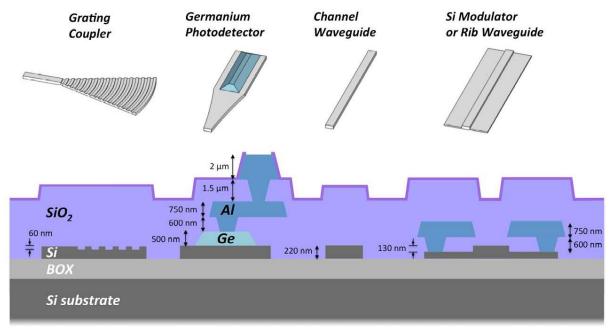


Si Photonics

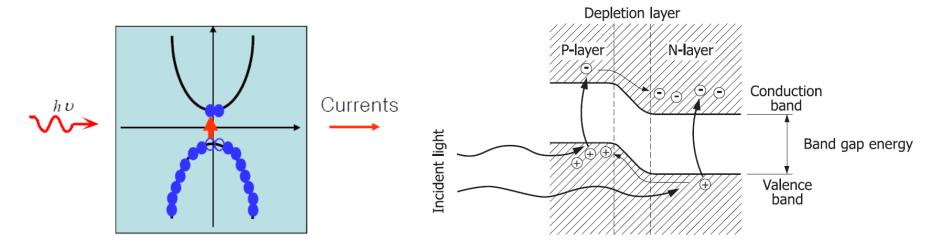
- Research topic for Si photonics:
 - Photodetector: VPD, LPD (이정민)
 - Optical modulator: MZM, ring modulator (유병민, 반유진)
 - Passive devices: waveguide (strip, rib), coupler (grating, directional, edge), ...
- Fabrication plan:
 - 2013: OpSIS-IME 002
 - Others: Luxtera, IMEC, LETI, IHP, ...





Si Photonics - Photodetector

- What is a <u>photodetector</u>?
 - Photodetection: absorption (Eg < hv) → current generation

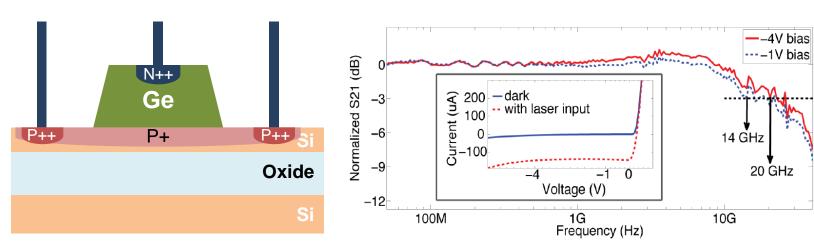


- E-O conversion: high electric field present in the depletion region → photo-generated carriers → photocurrent
- High-speed photodetector in optical receiver
 Realize high-speed optical interconnection



Si Photonics - Photodetector

Vertical photodetector (VPD)



Specification

Bias	DC responsivity @ 1550 nm	Bandwidth	Darkcurrent
-1 V	0.49 A/W	13.1 GHz	428 nA
-4 V	0.54 A/W	20.2 GHz	4.8 μΑ

Design consideration for high speed and responsivity



Research Plan in 2013

- Chip-to-chip interconnect
 - PD + TIA
 - Modulator + Modulator driver
 - 20-GHz board design with MKo and KDH
- On-chip electrical coupler design for SSB modulation
 - Objective: to generate 90 degree phase shift signal for SSB
 - Type: CPW coupler, ...
 - Considerations: size, phase tolerance
- Establish optical measurement setup (SAIT)
 - Optical probe stage, fiber array, ...
- Conference (2012)
 - ISOCC, "60-GHz Voltage-Controlled Oscillator and Frequency Divider in 0.25-µm SiGe BiCMOS Technology", Nov, 2012